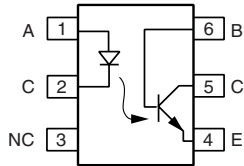


## Optocoupler, Phototransistor Output, with Base Connection



21842



i179004-5

### DESCRIPTION

The 4N25 family is an industry standard single channel phototransistor coupler. This family includes the 4N25, 4N26, 4N27, 4N28. Each optocoupler consists of gallium arsenide infrared LED and a silicon NPN phototransistor.

### FEATURES

- Isolation test voltage 5000 V<sub>RMS</sub>
- Interfaces with common logic families
- Input-output coupling capacitance < 0.5 pF
- Industry standard dual-in-line 6 pin package
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### APPLICATIONS

- AC mains detection
- Reed relay driving
- Switch mode power supply feedback
- Telephone ring detection
- Logic ground isolation
- Logic coupling with high frequency noise rejection

### AGENCY APPROVALS

- UL1577, file no. E52744
- BSI: EN 60065:2002, EN 60950:2000
- FIMKO: EN 60950, EN 60065, EN 60335

ORDER INFORMATION	
PART	REMARKS
4N25	CTR > 20 %, DIP-6
4N26	CTR > 20 %, DIP-6
4N27	CTR > 10 %, DIP-6
4N28	CTR > 10 %, DIP-6

ABSOLUTE MAXIMUM RATINGS (1)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT</b>				
Reverse voltage		V <sub>R</sub>	5	V
Forward current		I <sub>F</sub>	60	mA
Surge current	t ≤ 10 μs	I <sub>FSM</sub>	3	A
Power dissipation		P <sub>diss</sub>	100	mW
<b>OUTPUT</b>				
Collector emitter breakdown voltage		V <sub>CEO</sub>	70	V
Emitter base breakdown voltage		V <sub>EBO</sub>	7	V
Collector current		I <sub>C</sub>	50	mA
	t ≤ 1 ms	I <sub>C</sub>	100	mA
Power dissipation		P <sub>diss</sub>	150	mW



ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>COUPLER</b>				
Isolation test voltage		V <sub>ISO</sub>	5000	V <sub>RMS</sub>
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Isolation thickness between emitter and detector			≥ 0.4	mm
Comparative tracking index	DIN IEC 112/VDE 0303, part 1		175	
Isolation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C	R <sub>IO</sub>	10 <sup>12</sup>	Ω
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	10 <sup>11</sup>	Ω
Storage temperature		T <sub>stg</sub>	- 55 to + 125	°C
Operating temperature		T <sub>amb</sub>	- 55 to + 100	°C
Junction temperature		T <sub>j</sub>	125	°C
Soldering temperature <sup>(2)</sup>	max.10 s dip soldering: distance to seating plane ≥ 1.5 mm	T <sub>slid</sub>	260	°C

### Notes

<sup>(1)</sup> T<sub>amb</sub> = 25 °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

<sup>(2)</sup> Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS <sup>(1)</sup>							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>							
Forward voltage <sup>(2)</sup>	I <sub>F</sub> = 50 mA		V <sub>F</sub>		1.3	1.5	V
Reverse current <sup>(2)</sup>	V <sub>R</sub> = 3 V		I <sub>R</sub>		0.1	100	μA
Capacitance	V <sub>R</sub> = 0 V		C <sub>O</sub>		25		pF
<b>OUTPUT</b>							
Collector base breakdown voltage <sup>(2)</sup>	I <sub>C</sub> = 100 μA		BV <sub>CBO</sub>	70			V
Collector emitter breakdown voltage <sup>(2)</sup>	I <sub>C</sub> = 1 mA		BV <sub>CEO</sub>	30			V
Emitter collector breakdown voltage <sup>(2)</sup>	I <sub>E</sub> = 100 μA		BV <sub>ECO</sub>	7			V
I <sub>CEO</sub> (dark) <sup>(2)</sup>	V <sub>CE</sub> = 10 V, (base open)	4N25			5	50	nA
		4N26			5	50	nA
		4N27			5	50	nA
		4N28			10	100	nA
I <sub>CBO</sub> (dark) <sup>(2)</sup>	V <sub>CB</sub> = 10 V, (emitter open)				2	20	nA
Collector emitter capacitance	V <sub>CE</sub> = 0		C <sub>CE</sub>		6		pF
<b>COUPLER</b>							
Isolation test voltage <sup>(2)</sup>	Peak, 60 Hz		V <sub>IO</sub>	5000			V
Saturation voltage, collector emitter	I <sub>CE</sub> = 2 mA, I <sub>F</sub> = 50 mA		V <sub>CE(sat)</sub>			0.5	V
Resistance, input output <sup>(2)</sup>	V <sub>IO</sub> = 500 V		R <sub>IO</sub>	100			GΩ
Capacitance, input output	f = 1 MHz		C <sub>IO</sub>		0.6		pF

### Notes

<sup>(1)</sup> T<sub>amb</sub> = 25 °C, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

<sup>(2)</sup> JEDEC registered values are 2500 V, 1500 V, 1500 V, and 500 V for the 4N25, 4N26, 4N27, and 4N28 respectively.

CURRENT TRANSFER RATIO (1)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
DC current transfer ratio	$V_{CE} = 10\text{ V}, I_F = 10\text{ mA}$	4N25	$CTR_{DC}$	20	50		%
		4N26	$CTR_{DC}$	20	50		%
		4N27	$CTR_{DC}$	10	30		%
		4N28	$CTR_{DC}$	10	30		%

**Note**

(1) Indicates JEDEC registered values.

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Rise and fall times	$V_{CE} = 10\text{ V}, I_F = 10\text{ mA}, R_L = 100\ \Omega$	$t_r, t_f$		2		$\mu\text{s}$	

**TYPICAL CHARACTERISTICS**

$T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified



Fig. 1 - Forward Voltage vs. Forward Current

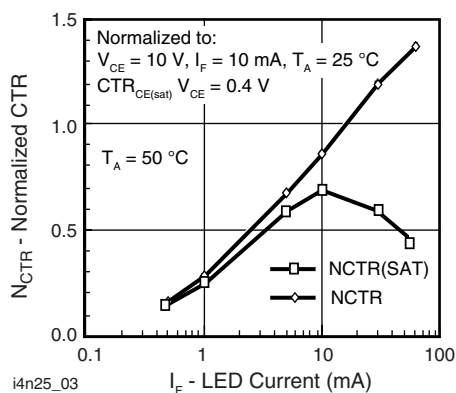


Fig. 3 - Normalized Non-Saturated and Saturated CTR vs. LED Current



Fig. 2 - Normalized Non-Saturated and Saturated CTR vs. LED Current

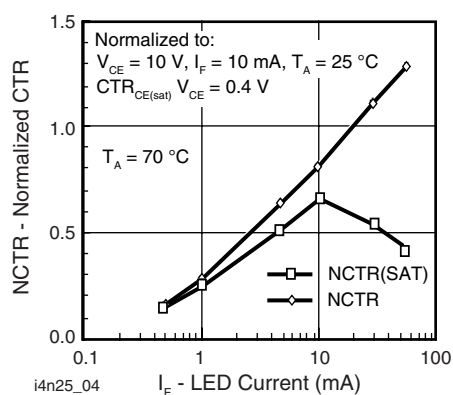


Fig. 4 - Normalized Non-Saturated and Saturated CTR vs. LED Current



Fig. 5 - Normalized Non-Saturated and Saturated CTR vs. LED Current

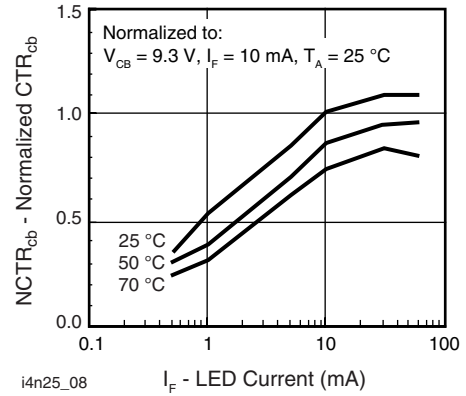


Fig. 8 - Normalized CTR<sub>cb</sub> vs. LED Current and Temperature



Fig. 6 - Collector Emitter Current vs. Temperature and LED Current

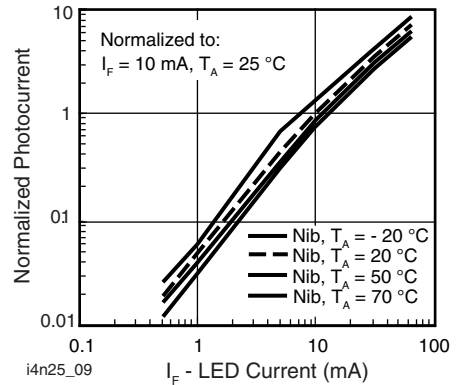


Fig. 9 - Normalized Photocurrent vs.  $I_F$  and Temperature

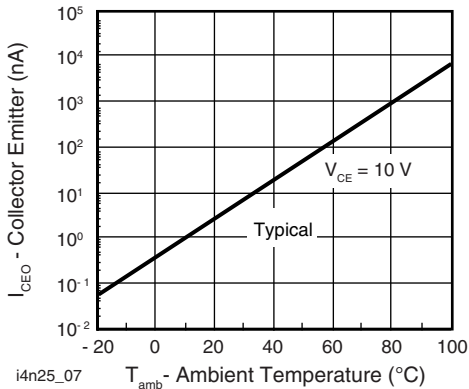


Fig. 7 - Collector Emitter Leakage Current vs. Temperature

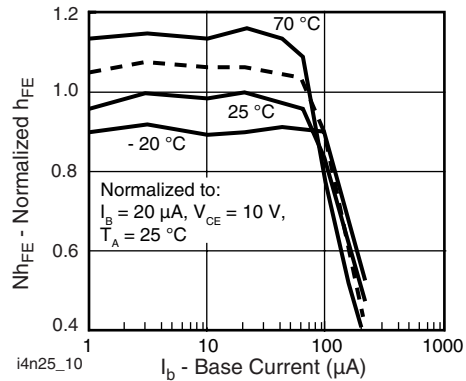


Fig. 10 - Normalized Non-Saturated  $h_{FE}$  vs. Base Current and Temperature

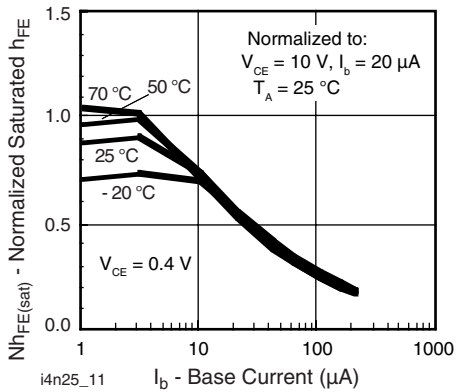


Fig. 11 - Normalized  $h_{FE}$  vs. Base Current and Temperature

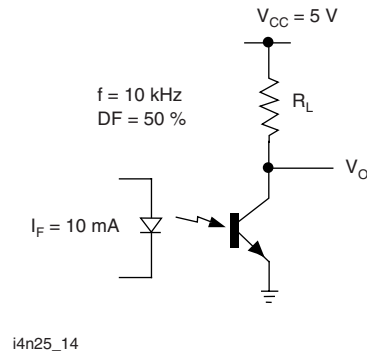
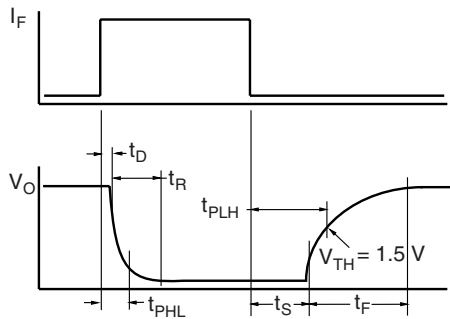


Fig. 14 - Switching Schematic



Fig. 12 - Propagation Delay vs. Collector Load Resistor



i4n25\_13

Fig. 13 - Switching Timing



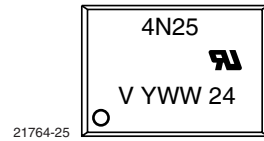
# 4N25, 4N26, 4N27, 4N28

Optocoupler, Phototransistor Output, Vishay Semiconductors  
with Base Connection

## PACKAGE DIMENSIONS in millimeters



## PACKAGE MARKING





## Disclaimer

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